

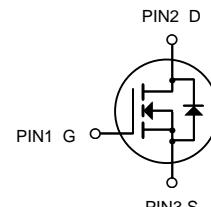


## Description

The Si2342DS-T1-GE3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23



N-Channel MOSFET

## Application

High power and current handing capability

Lead free product is acquired

Surface mount package

PWM applications

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
Si2342DS-T1-GE3	SOT-23	HXY MOSFET	3000

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current-Continuous	7	A
$I_{DM}$	Drain Current-Pulsed <sup>(Note 1)</sup>	32	A
$P_D$	Maximum Power Dissipation	2	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	120	$^\circ\text{C}/\text{W}$

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	20	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=0\text{V}$ ,	-	-	1.0	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Body Leakage Current	$V_{\text{DS}}=0\text{V}$ , $V_{\text{GS}}=\pm 12\text{V}$	-	-	$\pm 100$	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$ , $I_D=250\mu\text{A}$	0.5	0.75	1.2	V
$R_{\text{DS}(\text{on})}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{\text{GS}}=4.5\text{V}$ , $I_D=7\text{A}$	-	15	17	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}$ , $I_D=5\text{A}$	-	19	25	
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=10\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1.0\text{MHz}$	-	700	-	pF
$C_{\text{oss}}$	Output Capacitance		-	132	-	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		-	114	-	pF
$Q_g$	Total Gate Charge	$V_{\text{DS}}=10\text{V}$ , $I_D=4\text{A}$ , $V_{\text{GS}}=4.5\text{V}$	-	15	-	nC
$Q_{\text{gs}}$	Gate-Source Charge		-	2	-	nC
$Q_{\text{gd}}$	Gate-Drain("Miller") Charge		-	5.2	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DS}}=10\text{V}$ , $I_D=4\text{A}$ , $R_{\text{GEN}}=3\Omega$ , $V_{\text{GS}}=4.5\text{V}$	-	9	-	ns
$t_r$	Turn-on Rise Time		-	25	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	37	-	ns
$t_f$	Turn-off Fall Time		-	14	-	ns
$I_s$	Maximum Continuous Drain to Source Diode Forward Current		-	-	7.5	A
$I_{\text{SM}}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
$V_{\text{SD}}$	Drain to Source Diode Forward Voltage	$V_{\text{GS}}=0\text{V}$ , $I_s=8\text{A}$	-	-	1.2	V

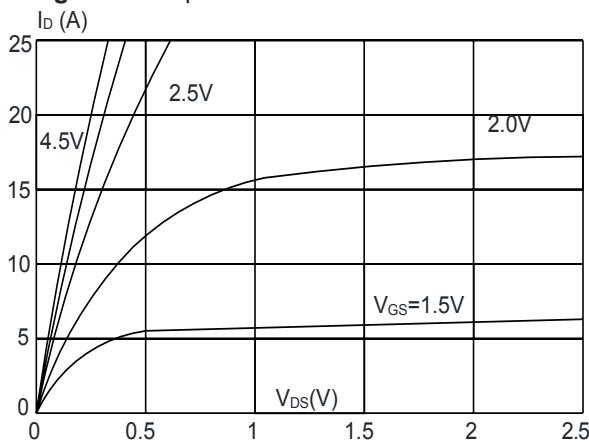
Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

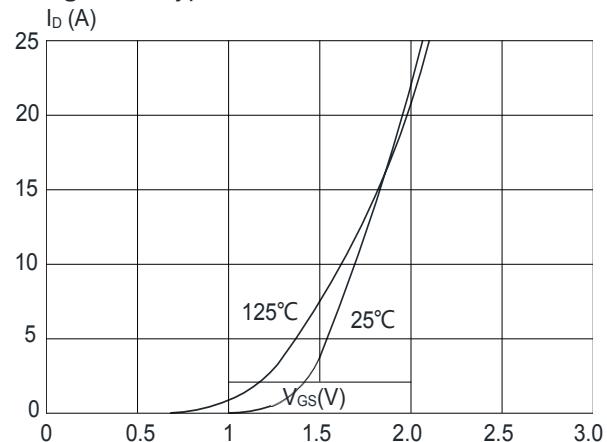


## Typical Performance Characteristics

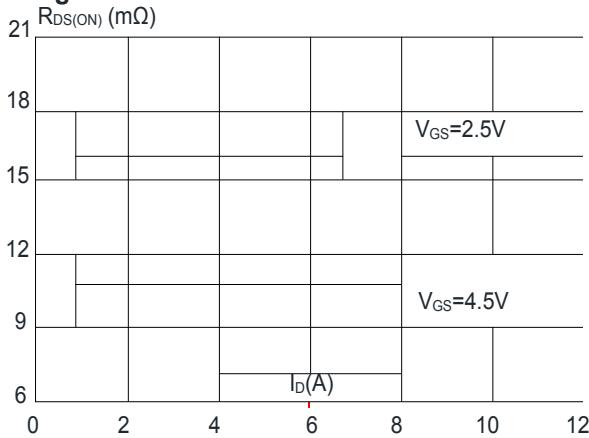
**Figure 1:** Output Characteristics



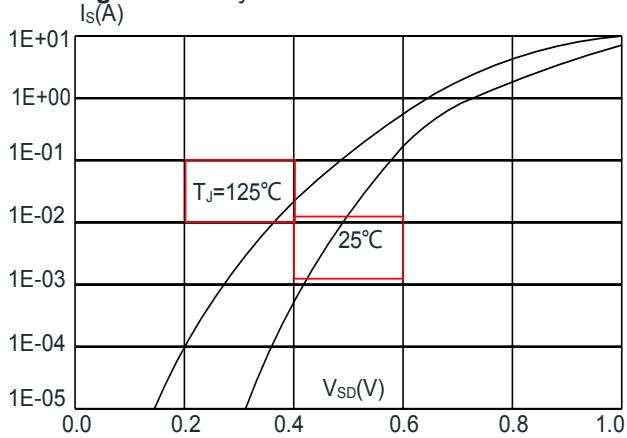
**Figure 2:** Typical Transfer Characteristics



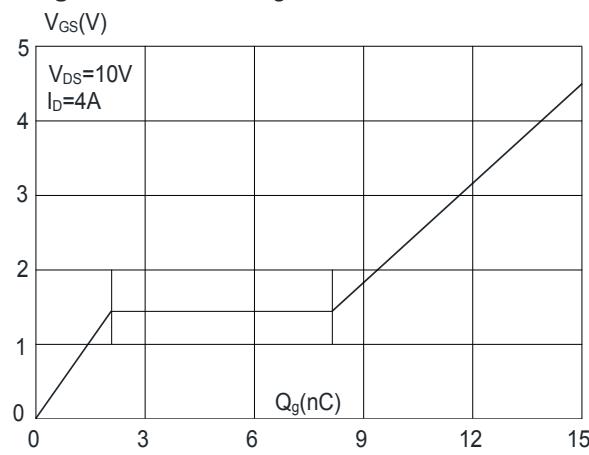
**Figure 3:** On-resistance vs. Drain Current



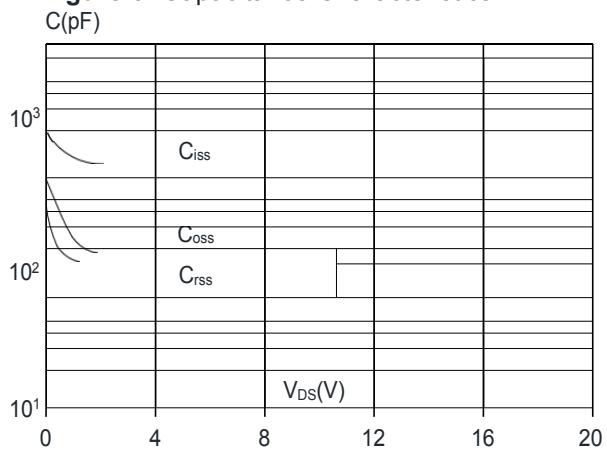
**Figure 4:** Body Diode Characteristics



**Figure 5:** Gate Charge Characteristics

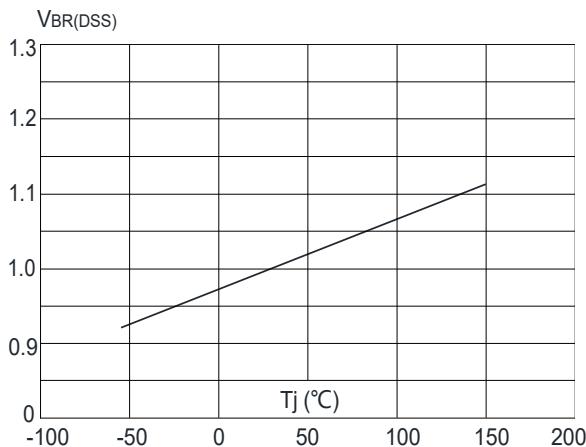


**Figure 6:** Capacitance Characteristics

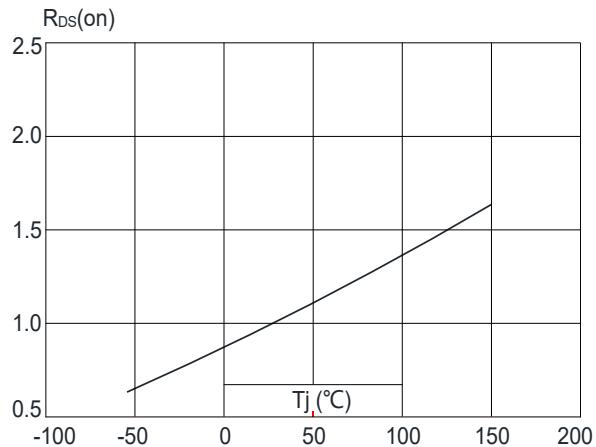




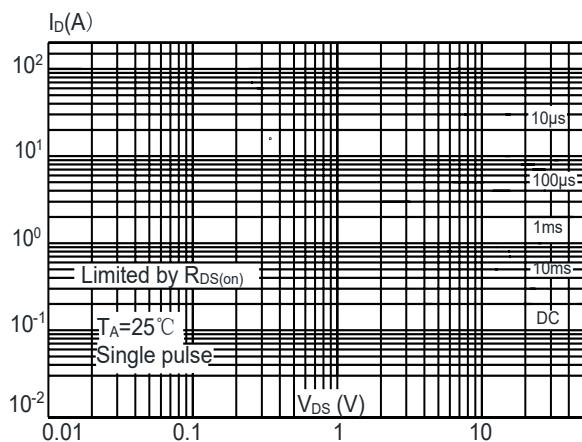
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



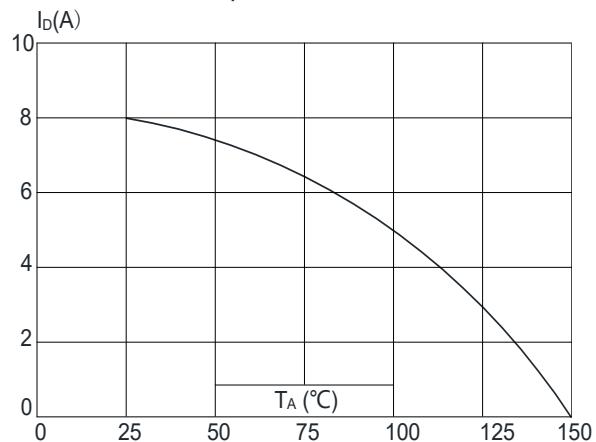
**Figure 8:** Normalized on Resistance vs. Junction Temperature



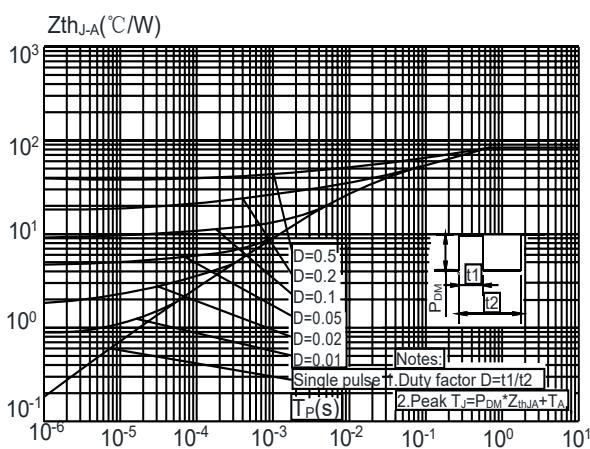
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

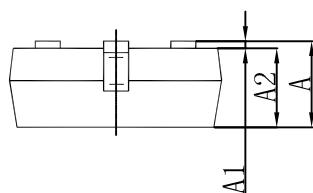
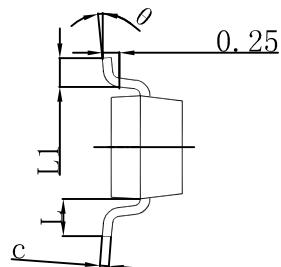
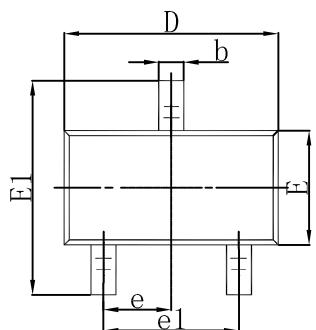


**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



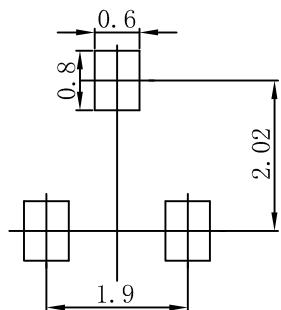


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension:in millimeters.
- 2.General tolerance: $\pm 0.05\text{mm}$ .
- 3.The pad layout is for reference purposes only.



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